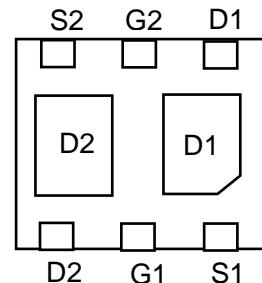


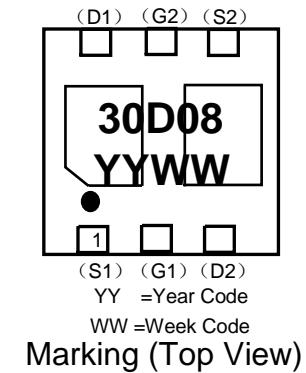
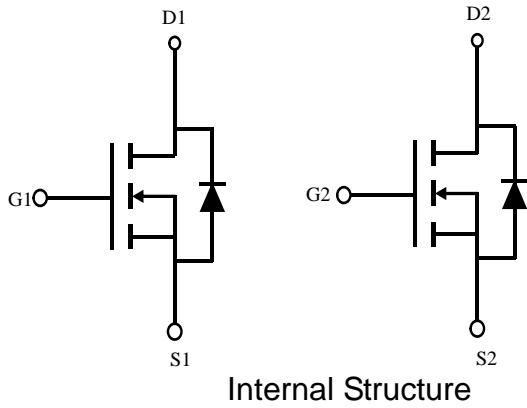
Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)
30	20@ V _{GS} =10V	7.6
	32@ V _{GS} =4.5V	



Bottom View(DFN2*2-6L)



Absolute maximum rating@25°C

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	7.6	A
Drain Current-Pulsed (Note1)	I _{DM}	30	A
Maximum Power Dissipation	P _D	1.8	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Thermal Characteristic

Parameter	Typical	Maximum	Units
Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	70	°C/W

Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu A, V_{GS} = 0V$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
Gate Threshold Voltage (Note3)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.6	2.4	V
Drain-Source On-State Resistance (Note3)	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 6A$		17	20	$m\Omega$
		$V_{GS} = 4.5V, I_D = 5A$		22	32	$m\Omega$
Forward Transconductance (Note3)	G_F	$V_{DS} = 5V, I_D = 5A$		15		S
Input Capacitance (Note4)	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V,$ $f = 1MHz$	-	255		pF
Output Capacitance (Note4)	C_{oss}		-	45		pF
Reverse Transfer Capacitance (Note4)	C_{rss}		-	35		pF
Turn-On Delay Time (Note4)	$t_{d(on)}$	$V_{DD} = 15V, R_L = 3\Omega,$ $V_{GS} = 10V, R_{GEN} = 3\Omega$	-	4.5		nS
Turn-On Rise Time (Note4)	t_r		-	2.5		nS
Turn-Off Delay Time (Note4)	$t_{d(off)}$		-	14.5		nS
Turn-Off Fall Time (Note4)	t_f		-	3.5		nS
Total Gate Charge (Note4)	Q_g	$V_{DS} = 15V, I_D = 5A,$ $V_{GS} = 10V$		5.2		nC
Gate-Source Charge (Note4)	Q_{gs}			0.85		nC
Gate-Drain Charge (Note4)	Q_{gd}			1.3		nC
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS} = 0V, I_S = 5A$			1.2	V
Diode Forward Current (Note 2)	I_S				5	A

Note 1: Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2: Surface Mounted on FR4 Board, $t \leq 10$ sec.

Note 3: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Note 4: Guaranteed by design, not subject to production

Typical Characteristics

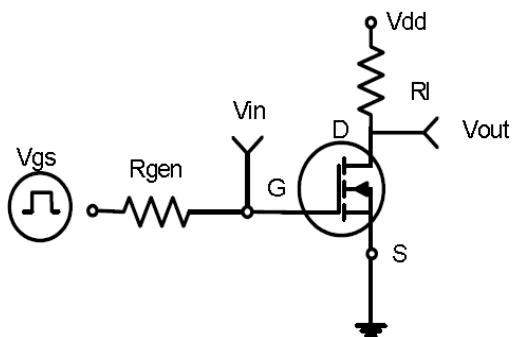


Fig 1. Switching Test Circuit

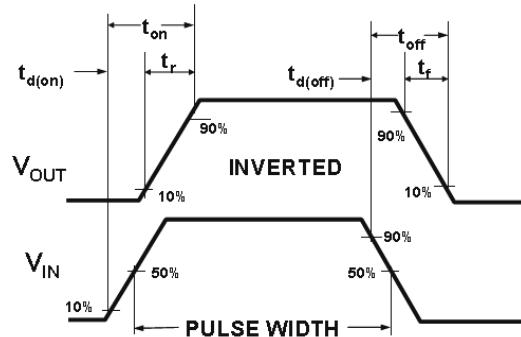


Fig 2. Switching Waveforms

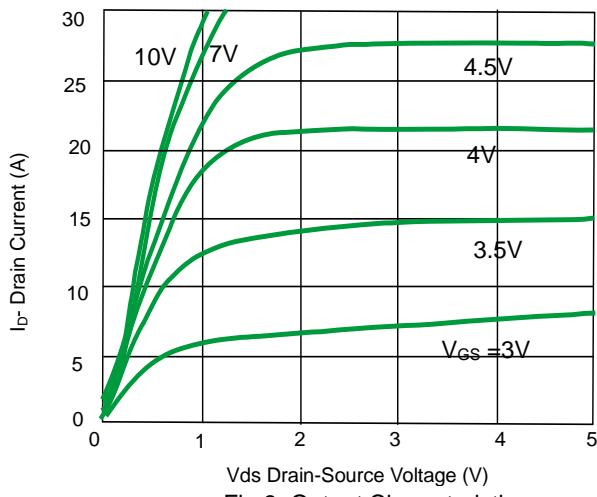


Fig 3. Output Characteristics

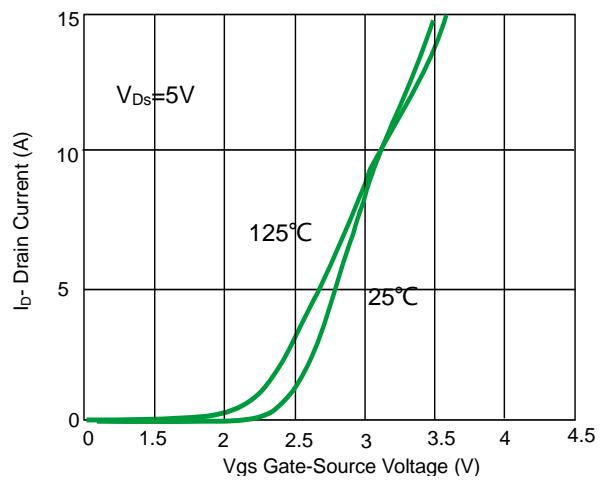


Fig 4. Transfer Characteristics

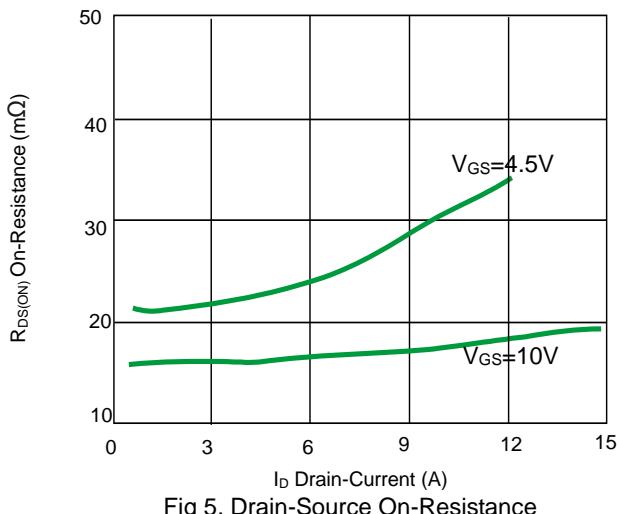


Fig 5. Drain-Source On-Resistance

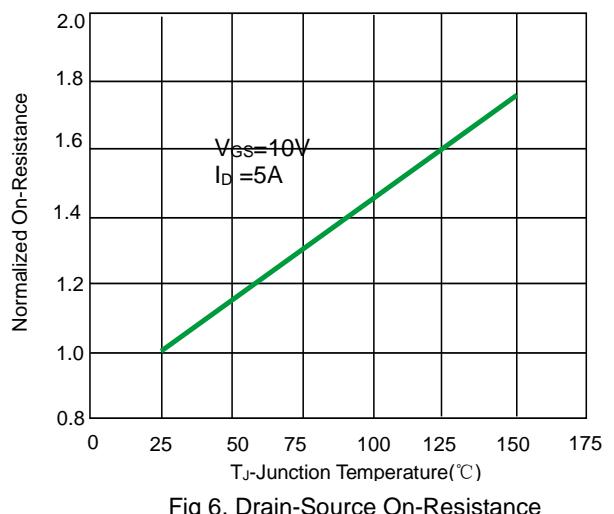


Fig 6. Drain-Source On-Resistance

Dual N-Channel MOSFET

PDNM6N30V7

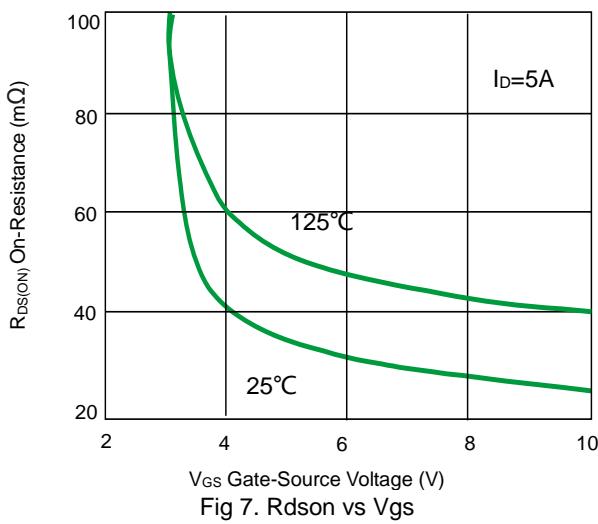


Fig 7. $R_{DS(on)}$ vs V_{GS}

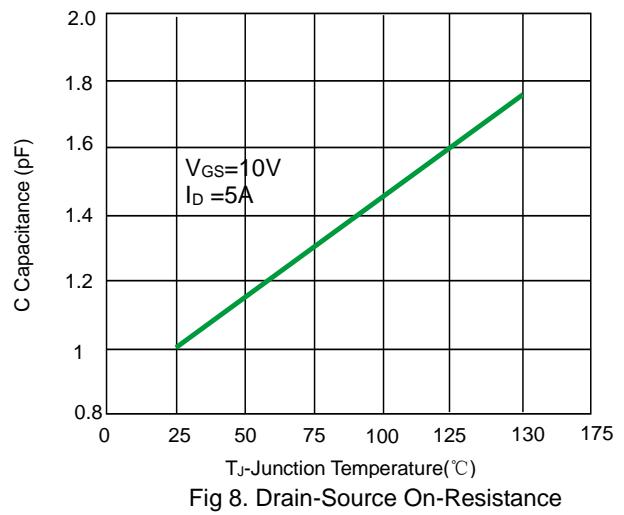


Fig 8. $R_{DS(on)}$ vs T_J

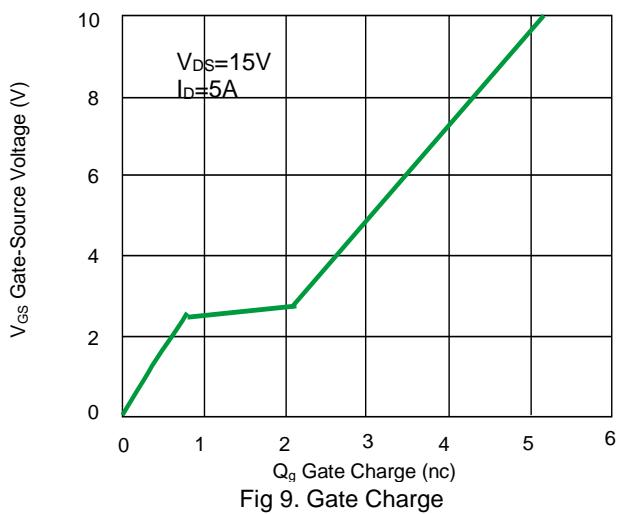


Fig 9. Gate Charge

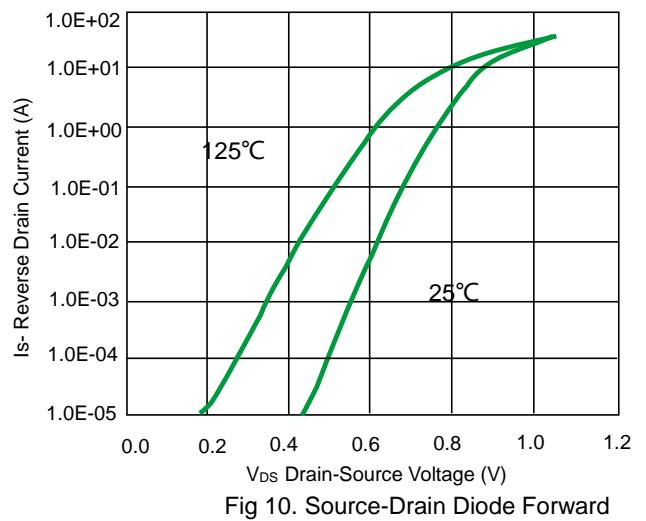


Fig 10. Source-Drain Diode Forward

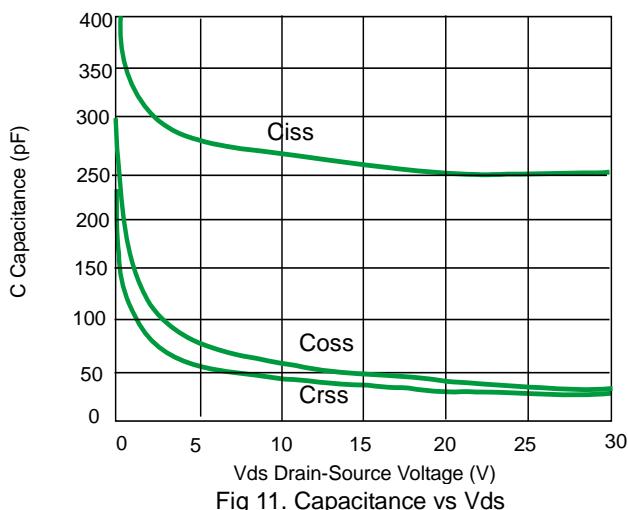


Fig 11. Capacitance vs V_{DS}

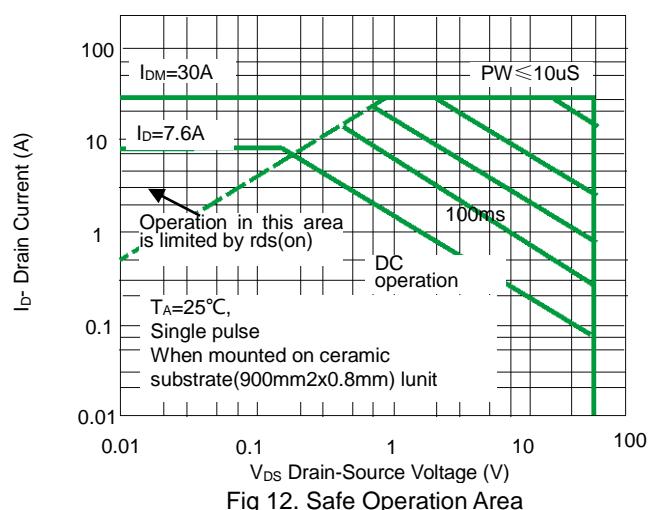


Fig 12. Safe Operation Area

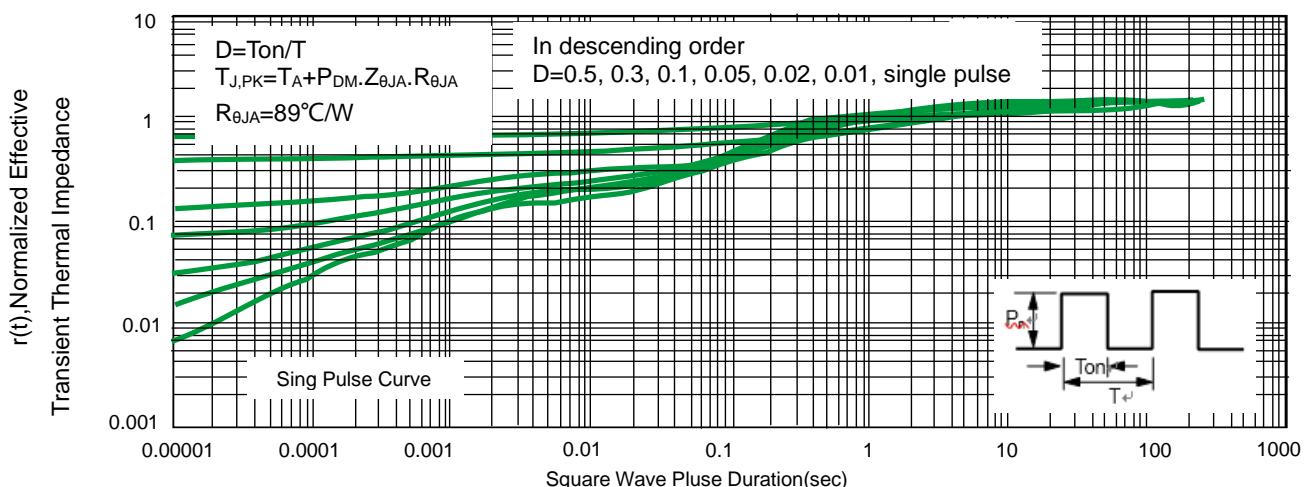
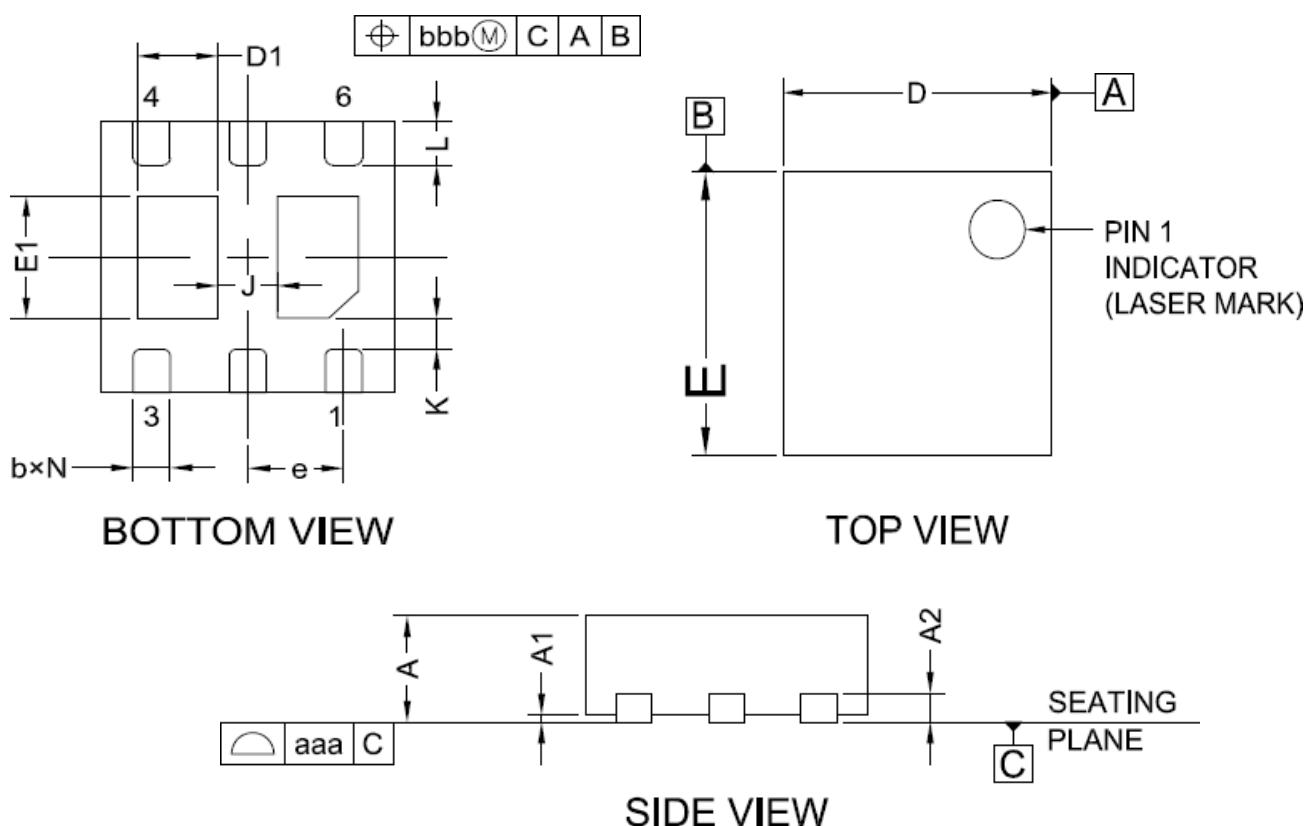
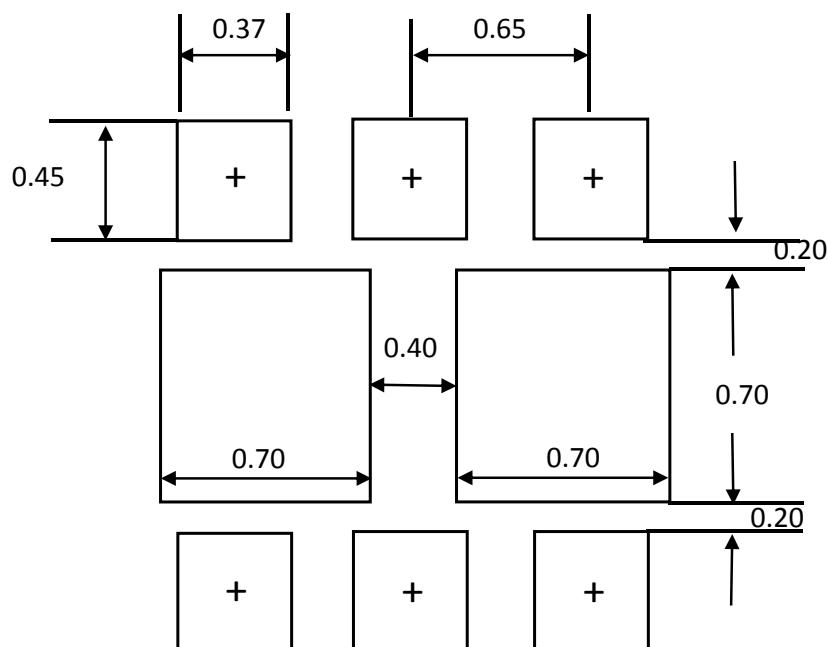


Fig 13. Normalized Maximum Transient Thermal Impedance

Product dimension(DFN2*2-6L)



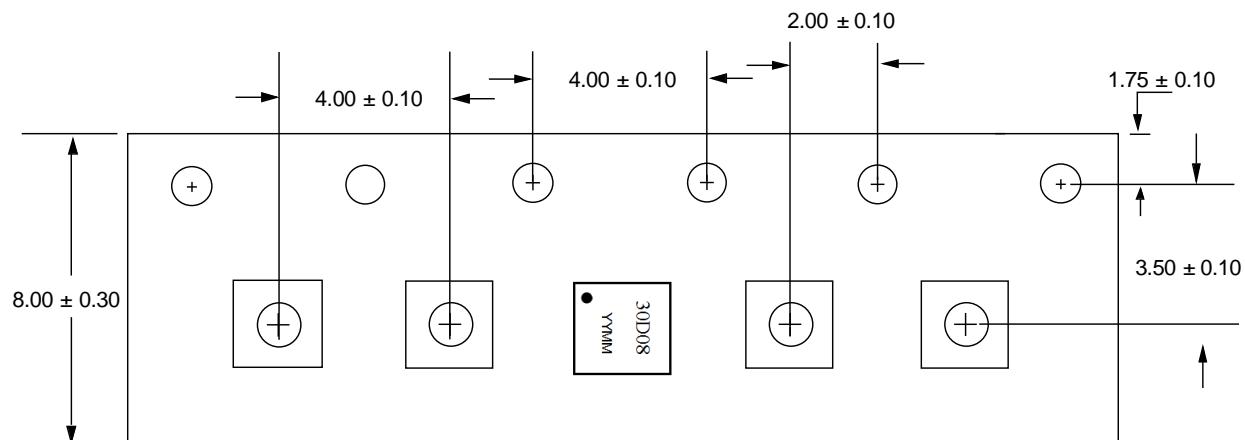
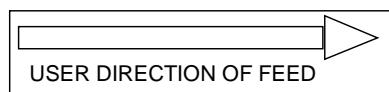
Dim	Millimeters		
	MIN	TYP	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2		0.203	
b	0.225	0.275	0.325
D	1.95	2.00	2.05
D1	0.50	0.55	0.60
E	1.95	2.00	2.05
E1	0.85	0.90	0.95
e		0.65BSC	
L	0.27	0.32	0.37
J		0.40BSC	
K		0.20MIN	
N		6	
aaa		0.08	
bbb		0.10	



Suggested PCB Layout

Ordering information

Device	Package	Shipping
PDNM6N30V7	DFN2*2-6L (Pb-Free)	3000 / Tape & Reel

Load with information

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